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Substitute for form 1449A/PTO				<i>Complete If Known</i>	
				Application Number	10/666,034
				Filing Date	September 18, 2003
				First Named Inventor	Kocon, Christopher Boguslaw
				Art Unit	2814
				Examiner Name	Long Pham
Sheet	1	of	12	Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
Examiner Initials <i>LP</i>	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	7	US-4,300,150	11-10-1981	Colak	
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	9	US-4,337,474	06-29-1982	Yukimoto	
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<p>Substitute for form 1449A/PTO</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(use as many sheets as necessary)</p>			<i>Complete If Known</i>	
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Sheet 2	of 12	Attorney Docket Number	018865-009010US	

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	49	US-5,268,311	12-07-1993	Euen et al.	
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		First Named Inventor	Kocon, Christopher Boguslaw
		Art Unit	2814
		Examiner Name	Long Pham
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		Attorney Docket Number	
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U.S. PATENT DOCUMENTS+

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
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LP	259	CN	1036666A		10-25-1989			<input checked="" type="checkbox"/>
	260	DE	4300806	C1	12-23-1993	Siemens AG		<input checked="" type="checkbox"/>
	261	DE	19736981	A1	08-20-1998	Mitsubishi Denki		<input checked="" type="checkbox"/>
	262	EP	0747967	B1	02-27-2002	ST Microelectronics Inc.		<input type="checkbox"/>
	263	EP	0975024	A2	01-02-2000	Fuji Electric Co. LTD.		<input type="checkbox"/>
	264	EP	1026749	A1	08-09-2000	Mitsubishi Denki Kabushiki		<input type="checkbox"/>
	265	EP	1054451	A2	11-22-2000	Intersil Corporation		<input type="checkbox"/>
	266	EP	1205980	A1	05-15-2002	Infineon Technologies AG		<input type="checkbox"/>
W	267	JP	01-192174	A	08-02-1989	Hitachi LTD.		<input checked="" type="checkbox"/>
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LP	269	JP	56-058267	A	05-21-1981	Nippon Teleg & Teleph Corp.	<input checked="" type="checkbox"/>
	270	JP	62-069562		03-30-1987	Mitsubishi Electric Corp.	<input checked="" type="checkbox"/>
	271	JP	63-186475		08-02-1988	Nissan Motor Co. LTD.	<input checked="" type="checkbox"/>
	272	JP	63-288047		11-25-1988	Toshiba Corp.	<input checked="" type="checkbox"/>
	273	JP	64-022051		01-25-1989	Matsushita Electric Ind	<input checked="" type="checkbox"/>
	274	JP	2000-040822		02-08-2000	Fuji Electric Co. LTD.	<input checked="" type="checkbox"/>
	275	JP	2000-040872		02-08-2000	Senju Metal IND CO LTD.	<input checked="" type="checkbox"/>
	276	JP	2000-156978	A	06-06-2000	Fuji Electric Co. LTD.	<input checked="" type="checkbox"/>
	277	JP	2000-277726	A	10-06-2000	Toshiba Corp.	<input checked="" type="checkbox"/>
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	281	JP	2001-102577	A	04-13-2001	Toshiba Corp.	<input checked="" type="checkbox"/>
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	283	JP	2001-135819	A	05-18-2001	Fuji Electric Co. LTD.	<input checked="" type="checkbox"/>
	284	JP	2001-144292	A	05-25-2001	Denso Corp.	<input checked="" type="checkbox"/>
	285	JP	2001-244461	A	09-07-2001	Toyota Central Res & Dev Lab INC.	<input checked="" type="checkbox"/>
	286	JP	2001-313391	A	12-20-2001	S. Takahiro et al.	<input checked="" type="checkbox"/>
	287	JP	2002-083976	A	03-22-2002	Naito et al.	<input checked="" type="checkbox"/>
	288	PCT	WO 00/33386	A2	08-08-2000	Koninklijke Philips Electronics	<input type="checkbox"/>
	289	PCT	WO 00/68997	A1	11-16-2000	C.P. Clare Corporation	<input type="checkbox"/>
	290	PCT	WO 00/68998	A1	11-16-2000	C.P. Clare Corporation	<input type="checkbox"/>
	291	PCT	WO 00/75965	A2	12-14-2000	General Semiconductor, Inc.	<input type="checkbox"/>
	292	PCT	WO 01/06550	A1	01-23-2001	Koninklijke Philips Electronics	<input type="checkbox"/>
	293	PCT	WO 01/06557	A1	01-25-2001	Koninklijke Philips Electronics	<input type="checkbox"/>
	294	PCT	WO 01/45155	A1	06-21-2001	Koninklijke Philips Electronics	<input type="checkbox"/>
	295	PCT	WO 01/59847	A2	08-16-2001	Koninklijke Philips Electronics	<input type="checkbox"/>
	296	PCT	WO 01/71815		09-27-2001	Koninklijke Philips Electronics	<input type="checkbox"/>
✓	297	PCT	WO 01/95385	A1	12-13-2001	General Semiconductor, Inc.	<input type="checkbox"/>

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			Application Number	10/666,034
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			Art Unit	2814
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		Country Code ³	Number ⁴				
LP	288	PCT	WO 01/95398	A1	12-13-2001	General Semiconductor, Inc.	<input type="checkbox"/>
	299	PCT	WO 02/01644	A2	01-03-2002	Silicon Wireless Corporation	<input type="checkbox"/>
↓	300	PCT	WO 02/047171	A1	06-13-2002	International Rectifier Corporation	<input type="checkbox"/>
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LP	301	BAI et al., "Novel automated optimization of power MOSFET for 12V input, high-frequency DC-DC converter," <i>International Symposium on Power Semiconductors and ICs, Technical Digest</i> , (2003), pp. 366-369.			
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LP	317	"IR develops CoolMOS™ -equivalent technology, positions it at the top of a 3-tiered line of new products for SMPS.* International Rectifiers company information available at http://www.irf.com (1999) 3 pages total.			
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	326	PARK et al., "Lateral Trench Gate Super-Junction SOI-LDMOSFETs with Low On-Resistance," Institute for Microelectronics, University of Technology Vienna, Austria (2002), pp. 283-285.			
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	330	SHENOY et al. "Analysis of the Effect of Charge Imbalance on the Static and Dynamic Characteristic of the Super Junction MOSFET," <u>IEEE International Symposium on Power Semiconductor Devices</u> 1999, pp. 99-102 (1999).			
	331	SINGER "Empty Spaces in Silicon (ESS): An Alternative to SOI," <u>Semiconductor International</u> page 42, December 1999.			
✓	332	TABISZ et al., "A MOSFET resonant synchronous rectifier for high-frequency dc/dc converters," (1990) <u>Proc. IEEE Power Electronics Specialist Conf. (PESC)</u> , pp. 769-779.			

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L P	333	Technical Literature from Quester Technology, Model APT-4300 300mm Atmospheric TEOS/Ozone CVD System, (unknown date), 3 pages total.	
	334	Technical Literature from Quester Technology, Model APT-6000 Atmospheric TEOS-Ozone CVD System, (unknown date), 2 pages total.	
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V	340	YAMASHITA et al., "Conduction Power loss in MOSFET synchronous rectifier with parallel-connected schottky barrier diode, (July 1998) <i>IEEE Transactions on Power electronics</i> , Vol. 13, No. 4, pp. 667-673.	

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